1. General description

Logic level N-channel MOSFET in a small MLPAK33-WF package using Trench12 technology. This product has been designed and qualified to meet AEC-Q101 requirements delivering high performance and endurance.

2. Features and benefits

- · Logic-level compatible
- Trench12 MOSFET technology
- Efficient switching with soft body-diode recovery
- Automotive qualified to AEC-Q101 at 175°C
- · Side-wettable flanks for robust solder joints and automatic optical inspection

3. Applications

- LED lighting
- · DC-to-DC conversion
- · Solenoid, motor and other load switching
- · Circuit protection

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	-	100	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[1]	-	-	23	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	35	W
Static characte	ristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 5.5 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11		-	23	32	mΩ
Dynamic chara	cteristics						
Q_{GD}	gate-drain charge	I _D = 5.5 A; V _{DS} = 50 V; V _{GS} = 10 V; T _j = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>		-	2.3	-	nC
Source-drain diode							
Q _r	recovered charge	$I_S = 2.5 \text{ A}; \text{ d}I_S/\text{d}t = -100 \text{ A/}\mu\text{s};$ $V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}; T_j = 25 \text{ °C}$		-	32	-	nC

^{[1] 23} A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.



5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	1 2 3 4	
2	S	source		
3	S	source		D ±
4	G	gate		
5	D	drain		G (F)
6	D	drain		mbb076 S
7	D	drain	8 7 6 5	
8	D	drain	MLPAK33 (SOT8002-3)	

6. Ordering information

Table 3. Ordering information

Type number Package					
	Name	Description	Version		
BUK9Q32-100L	MLPAK33	plastic thermal enhanced surface mounted package with side-wettable flanks (SWF); mini leads; 8 terminals;pitch 0.65 mm; 3.3 x 3.3 x 0.8 mm body	SOT8002-3		

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK9Q32-100L	8AV

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Tj = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	100	V
V_{GS}	gate-source voltage			-20	20	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	35	W
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[1]	-	23	А
		V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 2</u>		-	16	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 °C$; Fig. 3		-	92	А
T _{stg}	storage temperature			-55	175	°C
T _j	junction temperature			-55	175	°C
Source-drain	diode					
I _S	source current	T _{mb} = 25 °C		-	23	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 ^{\circ}C$		-	92	А

Symbol	Parameter	Conditions		Min	Max	Unit
Avalanche rugg	edness					
E _{DS(AL)S}		I_D = 8.7 A; $V_{sup} \le 100$ V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped; t_p = 70 μs; Fig. 4	[2] [3]	-	39.3	mJ
I _{AS}	non-repetitive avalanche current	$V_{sup} \le 100 \text{ V}; V_{GS} = 10 \text{ V}; T_{j(init)} = 25 \text{ °C};$ $R_{GS} = 50 \Omega; Fig. 4$	[2] [3]	-	8.7	А

- [1] 23 A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.
- [2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
- [3] Refer to application note AN10273 for further information.

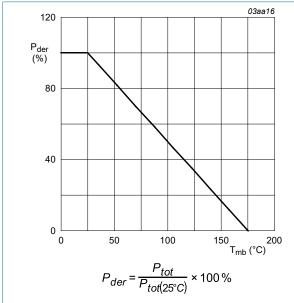


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

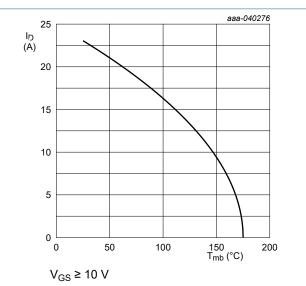


Fig. 2. Continuous drain current as a function of mounting base temperature

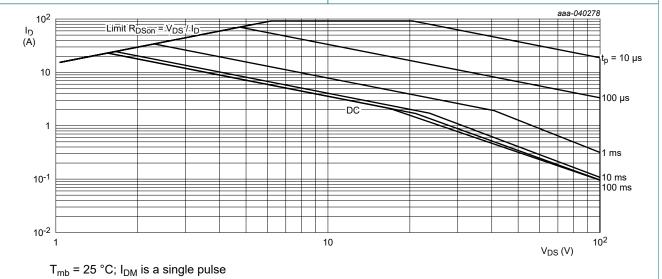
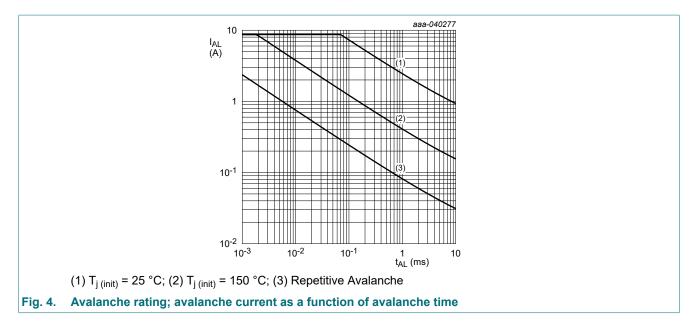


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

100 V, 32 mOhm logic level N-channel MOSFET in MLPAK33

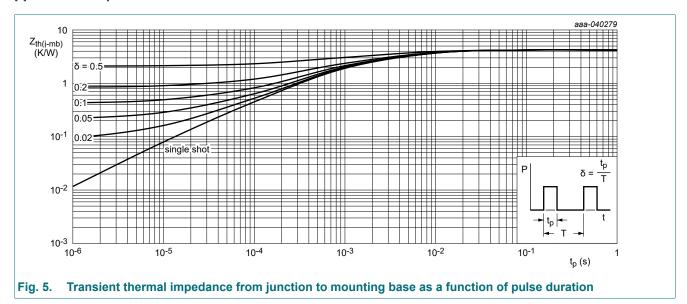


9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5		-	2.8	4.2	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient		[1]	-	40	-	K/W

[1] Device on 4 layer PCB. Refer to TN00008 for further information.



10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	100	115	-	V
	breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = -40 °C	97	112	-	V
		I _D = 250 μA; V _{GS} = 0 V; T _j = -55 °C	96	111	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}; Fig. 9;$ Fig. 10	1.45	1.7	2.15	V
I _{DSS}	drain leakage current	V _{DS} = 100 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μΑ
		V _{DS} = 100 V; V _{GS} = 0 V; T _j = 125 °C	-	-	20	μΑ
		V _{DS} = 100 V; V _{GS} = 0 V; T _j = 175 °C	-	-	200	μA
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-100	nA
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 5.5 A; T_j = 25 °C; Fig. 11	-	23	32	mΩ
		V_{GS} = 10 V; I_D = 5.5 A; T_j = 105 °C; Fig. 12	-	35	46	mΩ
		V_{GS} = 10 V; I_D = 5.5 A; T_j = 125 °C; Fig. 12	-	39	51	mΩ
		V_{GS} = 10 V; I_D = 5.5 A; T_j = 175 °C; Fig. 12	-	49	67	mΩ
		V _{GS} = 4.5 V; I _D = 5 A; T _j = 25 °C; <u>Fig. 11</u>	-	28	42.5	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 5 \text{ A}; T_j = 105 \text{ °C};$ Fig. 12	-	43	60	mΩ
		V_{GS} = 4.5 V; I_D = 5 A; T_j = 125 °C; Fig. 12	-	47	66	mΩ
		V_{GS} = 4.5 V; I_D = 5 A; T_j = 175 °C; Fig. 12	-	59	89	mΩ
R_{G}	gate resistance	f = 1 MHz; T _j = 25 °C	-	1.3	-	Ω
Dynamic ch	aracteristics					
Q _{G(tot)}	total gate charge	I_D = 5.5 A; V_{DS} = 50 V; V_{GS} = 10 V; T_j = 25 °C; Fig. 13; Fig. 14	-	19	29	nC
		I _D = 5.5 A; V _{DS} = 50 V; V _{GS} = 5 V; T _j = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>	-	10	-	nC
Q _{GS}	gate-source charge	I _D = 5.5 A; V _{DS} = 50 V; V _{GS} = 10 V;	-	3.1	-	nC
Q _{GD}	gate-drain charge	T _j = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>	-	2.3	-	nC
C _{iss}	input capacitance	V _{DS} = 50 V; V _{GS} = 0 V; f = 1 MHz;	-	1258	-	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 15</u>	-	205	-	pF
C _{rss}	reverse transfer capacitance		-	6	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = 50 V; R _L = 9.6 Ω; V _{GS} = 10 V;	-	4	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega; T_j = 25 °C$	-	3	-	ns
t _{d(off)}	turn-off delay time	1 –	-	19	-	ns
t _f	fall time		-	6	-	ns
Source-drai	in diode		1			
V _{SD}	source-drain voltage	I _S = 1.7 A; V _{GS} = 0 V; T _i = 25 °C; Fig. 16	-	0.77	1	V

100 V, 32 mOhm logic level N-channel MOSFET in MLPAK33

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t _{rr}	,	$I_S = 2.5 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$	-	44	-	ns
Q _r	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}; T_j = 25 \text{ °C}$	-	32	-	nC

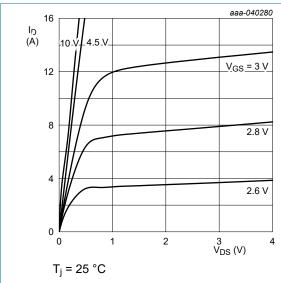


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

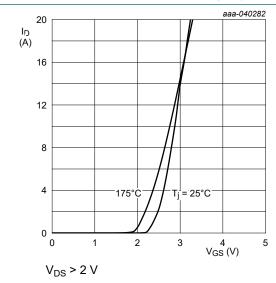


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

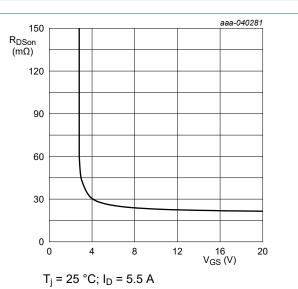


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

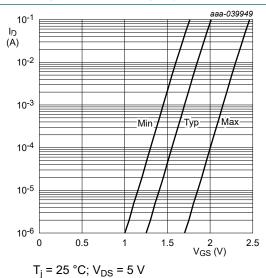


Fig. 9. Sub-threshold drain current as a function of gate-source voltage

100 V, 32 mOhm logic level N-channel MOSFET in MLPAK33

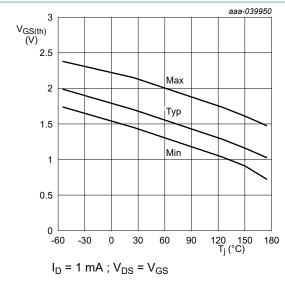


Fig. 10. Gate-source threshold voltage as a function of junction temperature

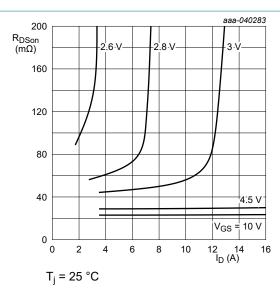


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

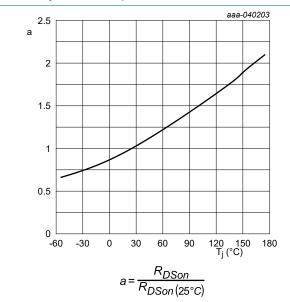


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

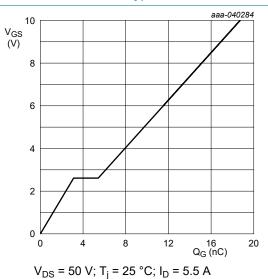


Fig. 13. Gate-source voltage as a function of gate

charge; typical values

100 V, 32 mOhm logic level N-channel MOSFET in MLPAK33

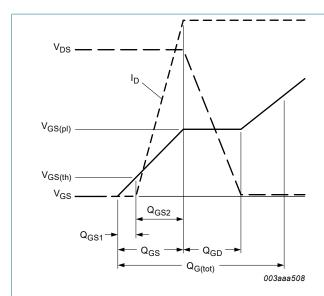
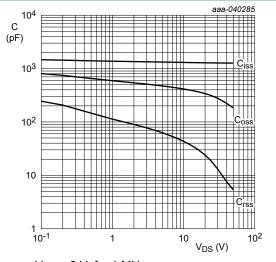


Fig. 14. Gate charge waveform definitions



 $V_{GS} = 0 V$; f = 1 MHz

Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

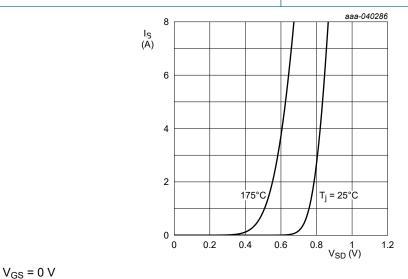


Fig. 16. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values

11. Package outline

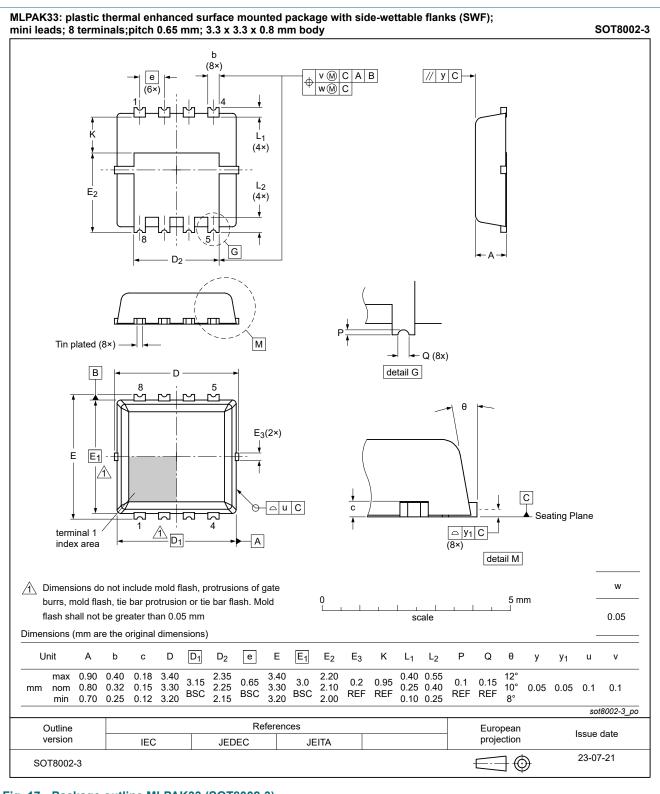
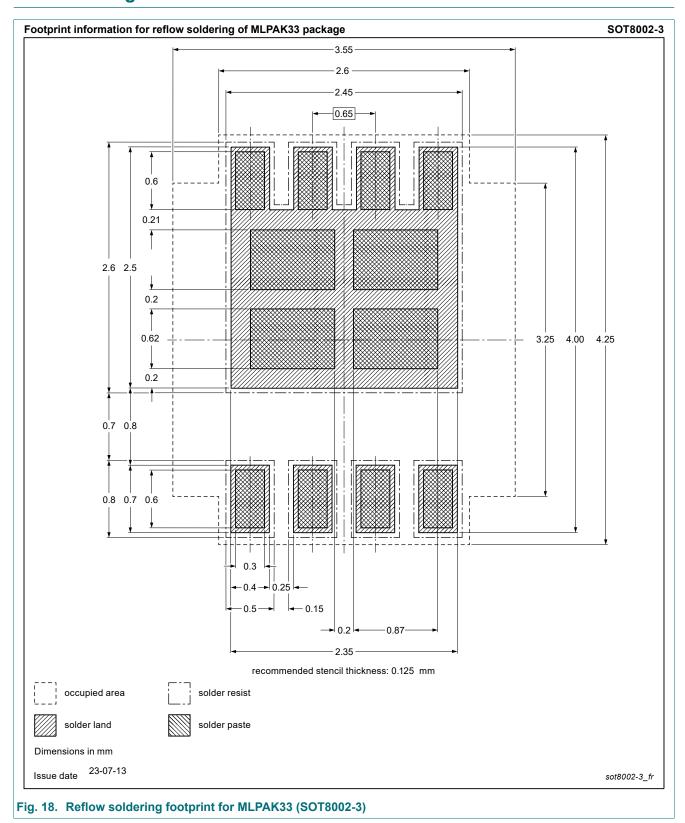


Fig. 17. Package outline MLPAK33 (SOT8002-3)

100 V, 32 mOhm logic level N-channel MOSFET in MLPAK33

12. Soldering



100 V, 32 mOhm logic level N-channel MOSFET in MLPAK33

13. Legal information

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Document status [1][2]	Product status [3]	Definition
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BUK9Q32-100L

Nexperia

100 V, 32 mOhm logic level N-channel MOSFET in MLPAK33

BUK9Q32-100L

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